



Discrete Power Semis and Modules

Article Archive

This document is a list of articles about discrete power semiconductors and power semiconductor modules published in the How2Power Today newsletter. Products listed here include:

- Power MOSFETs
- IGBTs
- SCRs/thyristors
- Diodes and rectifiers
- Power MOSFET modules
- IGBT modules
- Intelligent power modules
- Gate driver + MOSFET modules

Products are listed here using the following format:

Issue date:

Article title, Part number/product name

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For articles on power ICs, see the Power ICs Article Archives—one lists products by issue and the other by part number.

April 2016:

650-V GaN FET Delivers Low On-Resistance In TO-247, Transphorm's
TPH3207WS GaN FET

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Integrated Power Stages Raise Efficiency Of VR Solutions, Infineon
Technologies' Integrated Power Stage family

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May 2016:

600-V GaN FET Power Stage Promises Performance Boost And Reliability,
Texas Instruments' LMG3410 GaN FET power stage

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1200-V SiC MOSFETs Deliver Dramatic Improvements Versus Silicon IGBTs,
Infineon's CoolSiC MOSFETs and modules

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Embedded Component Packaging Leads To Tiny GaN Transistors, AT&S's
Embedded Component Technology

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June 2016:

1200-V Full SiC Module Boasts More-Efficient High-Frequency Operation,
ROHM Semiconductor's BSM180D12P3C007 SiC power module

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Discrete And Bare Die IGBTs Target Hybrid And All-Electric Vehicles,
Fairchild Semiconductor's FGY160T65SPD_F085 and FGY120T65SPD_F085 discrete IGBTs, PCGA200T65NF8, PCRKA20065F8, PCGA300T65DF8, and PCRKA30065F8 bare die IGBTs and diodes, and an automotive-grade module

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All-SiC Half-Bridge Power Module Features Highly Optimized Package Design, Wolfspeed's CAS325M12HM2 62-mm power module

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January 2015:

4-mm x 5-mm Power Block Provides Another Option For Shrinking DC-DC Designs, International Rectifier's IRFH4257D dual power MOSFET

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Intelligent Power Modules Are Optimized For Embedded Motor Drives And Inverters , Rohm Semiconductor's family of IPMs

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February 2015:



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1200-V SiC MOSFET Features <290-m Ω On-Resistance To 200°C,
STMicroelectronics' SCT20N120 SiC MOSFET

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March 2015:

GaN FETs + Driver Module Lowers Barriers To GaN-Based Power Design,
Texas Instruments' LMG5200 integrated half-bridge GaN FET power-stage

[For more details...](#)

SiC MOSFETs Miniaturize Ultra-High Voltage Pulse Generators, *ROHM's SCT2080KE SiC MOSFET*

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April 2015:

Top Five Products And Demos Seen at APEC 2015

- Cree's SiC-Module-Based 50-kW String PV Inverter
- Fairchild's New Extended Temperature Mid-Voltage MOSFETs Rated at 175° C

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May 2015:

GaN Transistors Are Cheaper Than Silicon, *Efficient Power Conversion's EPC2035 and EPC2036 eGaN power transistors*

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June 2015:

9.5-kV Light-Triggered Thyristor Integrates Forward Recovery Protection,
Infineon Technologies Bipolar's Light-triggered thyristor

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Enhancement-mode GaN transistor Boasts 60-A Rating, *GaN Systems' GS65516T 60-A 650-V GaN transistor*

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July 2015:

900-V SiC MOSFET Outperforms Superjunction Silicon MOSFETs, Cree's C3M0065090J SiC MOSFET

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IGBT Modules Are Configurable For A Wide Range Of Applications, Powerex Integrated Power Modules (PIPMs)

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September 2015:

Power MOSFETs Feature Low Turn-Off Losses, STMicroelectronics' MDMesh M2 EP power MOSFETs

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November 2015:

Super-Junction Power MOSFETs Move Up To 1500 V, STMicroelectronics' MDmesh K5 superjunction MOSFETs

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December 2015:

High-Temp SiC Power Modules Offer Different Configurations, Current Ratings, CISSOID's CHT-PLUTO and CHT-EUROPA SiC power modules

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February 2014:

Package Innovation Shrinks 650-V And 800-V MOSFETs Into 5- x 6-mm Footprint, STmicroelectronics' PowerFLAT 5x6 HV and VHV packages

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March 2014:

100-V eGaN FET Benefits Power Switching And RF Applications, Efficient Power Conversion's EPC8010 power transistor

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April 2014:

1200-V SiC Power MOSFET Boasts 200°C Rating, STMicroelectronics' SCT30N120 SiC MOSFET

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Driver Stage Tailors Power Conversion Solution To High-Performance FPGAs, Altera's ET4040 monolithic 40-A driver plus synchronous MOSFET powertrain

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600-V GaN Devices Are Offered In PQFNs Plus TO-220s For Low-Power Designs, Transphorm's TPH3002LD and TPH3002LS 600-V GaN HEMT devices in PQFNs and TPH3002PD and TPH3002PS 600-V GaN HEMT devices in TO-220s

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June 2014:

1200-V SiC MOSFET Lowers On-Resistance To 25-mΩ In TO-247, Cree's C2M0025120D SiC MOSFET

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July 2014:

25-A Phase-Control Stud-Style Thyristors Come In TO-48 Packages, America Semiconductor's 25RIA series phase-control thyristors

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October 2014:

All-SiC Half-bridge Module Reduces Cost And Size For Inverters, Cree's CAS300M17BM2 all-SiC 1.7-kV half-bridge power module

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Monolithic eGaN Half Bridge Boosts Efficiency For Buck Converters, Efficient Power Conversion's EPC2100 eGaN half bridge

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November 2014:

1200-V And 1700-V SiC Junction Transistors Are Positioned To Challenge SiC MOSFETs And Silicon IGBTs, GeneSiC Semiconductor's 1700-V SiC junction transistors (SJTs)—the GA50JT17-247 (25 mΩ), GA16JT17-247 (65 mΩ), and GA04JT17-247 (220 mΩ) —and 1200-V SJTs—the GA50JT12-247 (25 mΩ), GA20JT12-247 (60 mΩ), GA10JT12-247 (120 mΩ), and GA05JT12-247 (210 mΩ)
[For more details...](#)

December 2014:

Reverse-Conducting IGBTs Combine Strengths Of IGBTs And MOSFETs For High-Current Applications, IXYS's line of 3600-V reverse-conducting IGBTs
[For more details...](#)

January 2013:

Power MOSFETs Feature Ultra-Low On-State Resistance, International Rectifier's StrongIRFET family of 40-V HEXFET MOSFETs
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April 2013:

Smart Bypass Diode Lowers Power Dissipation, Texas Instruments' SM74611 smart bypass diode
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Development Board Facilitates Design of High-Frequency Converters Using GaN Transistors, Efficient Power Conversion's EPC9010 development board, for evaluation of EPC's 100-V eGaN FETs
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High-Voltage Silicon Diodes Achieve Ultrafast Recovery, Infineon Technologies' Rapid 1 and Rapid 2 650-V fast-recovery silicon diode families
[For more details...](#)

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May 2013:

Fast-Switching Solid-State Relays Consume Ultra-Low Power, Electronic Design & Research's μ R2M and μ D2M series solid-state relays

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Precision N-Channel MOSFET Arrays Feature Zero Threshold Voltage, Advanced Linear Devices' ALD210800A/ALD210800 n-channel MOSFET arrays

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June 2013:

Intelligent Power Modules Reinforce Automotive Safety, Mitsubishi Electric's PM800CJG060G and PM500CJG120G J-series automotive IPMs

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August 2013:

GTO Thyristor Handles 500 A In Smaller Package, IXYS UK Westcode's S0500YC GTO thyristor

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October 2013:

Trench Technology Boosts Efficiency, New Package Saves Space For Rad-Hard MOSFETs, International Rectifier's R8 rad-hard trench MOSFETs

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Enhancement-Mode GaN FET Delivers Extremely Low On-Resistance, Efficient Power Conversion's EPC2018 eGaN FET

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November 2013:

High-Voltage Gate Driver Features Unique Monitoring Capabilities, Amantys' AP45CC1 IGBT gate driver

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January 2012:

Demo Suggests Cascode MOSFET Stacks up Well Against SiC And Si Switches, Alpha and Omega Semiconductor's and SemiSouth Laboratories' UniSiC 1200-V, 90-m Ω MOSFET

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Compound Power Devices Co-Package SiC Schottkys With MOSFETs Or IGBTs, Renesas Electronics' RJQ6020DPM, RJQ6021DPM, and RJQ6022DPM SiC compound power devices

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600-V SiC Schottky Targets Air Conditioners, Base Stations, And Solar Arrays, Renesas Electronics' RJS6005TDPP SiC Schottky barrier diode

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February 2012:

Power Device Enhances Scalability In Computing And Consumer Applications, International Rectifier's IR3551 50-A PowIRstage module

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April 2012:

Soft-Switching IGBT Replaces Relays In PTC Heaters For Hybrid And Electric Vehicles, International Rectifier's AUIRGDC0250 1200-V automotive-qualified IGBT for soft-switching applications

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May 2012:

50-A Power Devices Extend SiC Benefits To More Applications, Cree's family of 50-A SiC MOSFETs and Schottkys

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Power Modules Shrink Footprint For Appliances And Industrial Applications, International Rectifier's family of μ IPM power modules

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650-V 55-m Ω SiC JFETs Boast Extremely Low On-Resistance, SemiSouth Laboratories' SJDA065R055 SiC JFET power transistors

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July 2012:

MOSFET Delivers Low On-Resistance At 650 V, STMicroelectronics' STY139N65M5 650-V n-channel superjunction MOSFET

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September 2012:

High-Voltage GaN HEMT Achieves JEDEC Qualification, Transphorm's TPH2006PS 600-V GaN HEMT

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Super Junction MOSFETs Break New Ground At 900 V And 950 V, STMicroelectronics' SuperMESH 5 super junction MOSFETs

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October 2012:

Development Boards Simplify Evaluation Of eGAN FETs, Efficient Power Conversion's EPC9003 and EPC9006 development boards

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High-Speed 600-V IGBTs Feature Very Low Saturation Voltage, Advanced Power Electronics Corp.'s AP20GT60 n-channel IGBT family

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November 2012:

Robust High-Voltage MOSFETs Challenge Superjunction MOSFETs, Alpha and Omega Semiconductor's AlphaMOS II MOSFETs

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December 2012:

High-Voltage IGBT Modules Handle 4160-V AC Lines, Powerex's QID3320002 and QID4515002 dual HVIGBT modules

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January 2011:

1200-V Silicon Carbide MOSFET Aims To Replace Silicon Devices, Cree's CMF20120D 1200-V SiC power MOSFET

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New Package Shrinks MOSFETs for Hi-Rel Space Applications, International Rectifier's family of hermetic rad-hard 100-V MOSFETs in the new SMD0.2 package

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SiC Schottkys Support Power Supply Designs for More-Efficient Data Centers, Cree's Z-Rec 650-V SiC Schottky diodes

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February 2011:

MOSFETs Boost DC-DC Converter Efficiency Up To 2%, International Rectifier's DirectFETplus 25-V power MOSFETs

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MOSFET Boasts Micro-ohm On-resistance, Picor's PI5101 MOSFET

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Surface-Mount SiC Schottky Targets Solar Micro-inverters, Cree's C2D05120 1200-V SiC Schottky diode

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SiC JFETs Are Now Shipping in Commercial Quantities, SemiSouth Laboratories' SJEP120R100, SJEP120R063 and SJEP170R550 normally-off trench SiC power JFETs

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March 2011:

GaN Semiconductor Startup Demos 99% Efficient DC-DC Boost Converter, Transphorm's EZ-GaN technology

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Second-Gen GaN Transistors Feature Enhanced Performance, Lead-Free Packaging, Efficient Power Conversion's EPC2001 and EPC2015 enhancement-mode GaN-on-silicon FETs

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60-A Module Boasts Better Performance Than DrMOS and Other Power Devices, International Rectifier's IR3550 PowIRstage

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High-Voltage Superjunction MOSFET Enables High-Efficiency AC-DC Conversion, Alpha and Omega Semiconductor's AOTF27S60 600-V superjunction MOSFET

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CanPAK Family Adds Medium-Voltage MOSFETs, Infineon Technologies's 60-V to 150-V OptiMOS power MOSFETs

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May 2011:

High-Voltage Power Switch Features 225°C Operation, Logic-level Gate Control, Cissoid's CHT-Jupiter 600-V SiC power switch with logic-level gate drive

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Shielded Gate Lowers Losses For 60-V Trench FET, Fairchild Semiconductor's FDMS86500L N-channel, PowerTrench MOSFET

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Lower Current Rating And Price Extends SiC MOSFET Benefits To More Apps, Cree's CMF10120 24-A 1200-V SiC MOSFET

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600-V Fast IGBTs Reduce Inverter Size And Cost, Infineon Technologies IKD03N60RF and IKD04N60RF reverse-conducting IGBTs

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June 2011:

Power Module Targets Hybrid And Electric Vehicles, Mitsubishi Electric's CT300DJH060 J-Series transfer molded power module

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August 2011:

High-Temperature Components For Power Design

- 40-V GaN Transistor Is Fully Enhanced at Lower Gate Voltage, Efficient Power Conversion's EPC2014 eGaN FET
- New Source For Space-Grade Power MOSFETs, STMicroelectronics' STRH100N10, STRH8N10, STRH40P10, STRH100N6 and STRH40N6 rad-hard power MOSFETs
- SiC JFETs Target High-end Audio, SemiSouth Laboratories SJEP120R100A and SJEP120R063A SiC JFETs
- Automotive-qualified MOSFETs Deliver Low $R_{DS(ON)}$ For Heavy Loads, International Rectifier's AUIRF1404 and other 40-V to 75-V MOSFETs
- 1200-V SiC Schottkys Offer Higher Performance At Lower Cost, Cree's C4D02120x, C4D05120x, C4D10120x, C4D20120x and C4D40120x 1200-V Z-Rec SiC Schottky diodes
- Small-Signal Diode Operates To 225°C, CISSOID's CHT-GANYMEDE dual small-signal diode

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September 2011:

Power MOSFETs, IGBTs, And Modules

- Ultra-fast 1200-V IGBTs Target Induction Heating, International Rectifier's IRG7PH35UD1 and IRG7PH42UD1 trench IGBTs
- Ultra-fast 1200-V IGBTs Reduce Switching And Conduction Losses, International Rectifier's IRG7PH35xx, IRG7PH42xx, IRG7PH46xx, IRG7PH50x field-stop trench IGBTs
- 1200-V IGBTs Feature High Gain, High Speed, IXYS's IXYH50N120C3, IXYH82N120C3, IXYN82N120C3H1, and IXYB82N120C3H1 IGBTs
- 1200-V SiC JFET Power Module Is Offered As Standard Product, Microsemi's APTJC120AM13VCT1AG phase-leg SiC power module
- 1200-V SiC JFET Delivers Low On-Resistance, SemiSouth Laboratories' SJDP120R045 and SJDC120R045 normally on trench SiC power JFETs

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- *Power Modules Strengthen Safety, Increase Functionality For Electric Vehicles, Mitsubishi Electric's J-series new intelligent power modules (IPMs) and J-series transfer-molded power modules (T-PMs), models PM150CJG120G, PM300CJG060G, PM300CJG120G, PM600CJG060G, CT300DJH120, and CT600DJH060*
- *650-V MOSFETs Integrate Fast Body Diode For Higher Efficiency, Infineon Technologies' CFD2 650-V CoolMOS MOSFETs, model IPW65R080CFD*
- *Power Modules Are Tailored To All Major Solar Converter Topologies, Microsemi's power modules, models APTC60AM45BC1G, APTC60AM45B1G, APTC60AM83BC1G, APTC60AM83B1G, APTCV60HM45RCT3G, APTCV60HM45RT3G, APTCV60HM70RT3G, APTC60HM70RT3G, APTGT50H60RT3G, APTCV60HM45BC20T3G, APTCV60HM45BT3G, APTCV60HM70BT3G, APTGV50H60BT3G, APT5M65BBM19T3G, APTC60BBM24T3G, and APTGT100BB60T3G*
- *40-V To 600-V MOSFETs Are Optimized For Solar Microinverters, Alpha and Omega Semiconductor's AlphaMOS MOSFETs, models AOT240L, AOT260L, AOT290L, AOTF42S60, AOD11S60, and AOTF12N60FD*
- *Second-Gen 200-V GaN Transistor Delivers Enhanced Performance, Efficient Power Conversion's EPC2010 eGaN FET*
- *Trench MOSFETs Boost Efficiency In Synchronous Rectification Applications, Fairchild Semiconductor's FDP083N15A_F102, FDB082N15A and FDP036N10A 100-V and 150-V PowerTrench MOSFETs*
- *Development Board Eases Designs Based On 100-V GaN FETs, Efficient Power Conversion's EPC9006 development board for EPC2007 100-V eGaN FET*
- *Increased Voltage Ratings Extend MOSFET Benefits To More DC-DC Applications, STMicroelectronics' 60-V, 75-V, and 80-V STripFET VI DeepGATE power MOSFETs, models STP260N6F6, STH260N6F6-2, STP210N75F6, STH210N75F6-2, and STL75N8LF6*
- *P-Channel MOSFETs Improve Efficiency And Cut Costs In Automotive Designs, Infineon Technologies' OptiMOS P2 40-V family of trench power MOSFETs, 30 models including the IPD90P04P4-05*
- *Power MOSFETs For Automotive Reduce On-Resistance, STMicroelectronics' 30-V and 40-V STripFET VI DeepGATE power MOSFETs, 9 models*
- *Dual Asymmetric MOSFET Modules Push Power Density Higher, Fairchild Semiconductor's FDMS36xxS power-stage MOSFET modules*

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October 2011:

Diodes And Rectifiers

- *SiC Schottkys In DPAKs Offer 2-A To 10-A Ratings, Cree's C4D02120E, C4D05120E, C4D08120E, and C4D10120E 1200-V SiC Schottky diodes*
- *1200-V/5-A SiC Diodes Come In DPAK Packaging, SemiSouth Laboratories' SDB05S120 SiC diodes*
- *200-V Schottky Achieves Over 2-kV ESD Protection, STMicroelectronics STPS60SM200C 200-V Schottky diode*
- *Low-VF Schottkys Come In Space-Saving Package, Central Semiconductor's CTLSH01-30 and CTLSH01-30L low-V_F Schottky diodes*
- *600-V Rectifiers Deliver Over 10 A In DPAK Package, Vishay Intertechnology's 200-V and 600-V FRED Pt Hyperfast and Ultrafast rectifiers, 18 models including models VS-12EWH06FNx-M3, VS-15AWL06FNx-M3, VS-15EWL06FNx-M3, VS-15EWH06FNx-M3, and VS-15EWX06FNx-M3*

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IGBTs Deliver Power Savings, Higher-Temperature Operation, Powerex's S-series 300-A to 800-A, 1200-V IGBTs, models CM300DY-24S, CM450DY-24S, CM600DY-24S, and CM800DY-24S

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Gate-Driver Evaluation Board For SiC Power Modules, SemiSouth Laboratories' SGDR2500P2 optoisolated gate-driver board

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November 2011:

Gate Drive Enhances Performance, Design Reuse In Medium- And High-Voltage Applications, Amantys Power Drive for 3.3-kV IGBT modules

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IGBT Integrates Freewheeling Diode For Small Size In Induction Heating, Toshiba Electronics Europe's GT40QR21 1200-V IGBT

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December 2011:

Half-Bridge Power Modules Feature Small Footprint, Vincotech's flowPHASE 0 2nd Generation family of half-bridge power modules

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Trench-Based 100-V Schottkys Outperform Planars, ON Semiconductor's NTST30100CTG, NTST20100CTG and NTSB20U100CTG low-forward-voltage (LVFR) Schottky rectifiers

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January 2010:

MOSFETs Take Top-Side Cooling A Step Further, CSD16407Q5C, CSD16408Q5C, CSD16325Q5C, CSD16321Q5C, and CSD16322Q5C DualCool NexFET MOSFETs from Texas Instruments

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February 2010:

DirectFETs Are Qualified for Automotive, International Rectifier's AUIRF7739L2 and AUIRF7665S2 AEC-Q101 qualified DirectFET2 power MOSFETs

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MOSFETs Boast Lower FOM at 200 V and 250 V, Infineon Technologies' OptiMOS power MOSFETs

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March 2010:

GaN Power Transistors Seek To Replace Silicon Power MOSFETs, Efficient Power Conversion's enhancement-mode GaN-on-silicon power transistors, models EPC1014, EPC1015, EPC1009, EPC1005, EPC1007, EPC1001, EPC1013, EPC1011, EPC1012, and EPC1010

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GaN-Based Power Stages Look To Reshape Point-of-Load Landscape, International Rectifier's iP2010 and iP2011 GaN-based power stage devices

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April 2010:

SiC Schottkys Push Voltage Ratings to 1700 V, Cree's CPW3-1700S010B and CPW3-1700S025B Z-Rec 1700-V junction barrier Schottky diodes

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Tiny MOSFETs Deliver Low On-Resistance For Load Switching, Alpha and Omega Semiconductor's AON7428 and AON7405 30-V power MOSFETs

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May 2010:

Automotive MOSFETs Promise Low $R_{DS(on)}$ and Durability, International Rectifier's family of automotive-qualified MOSFETs, 22 models including AU1RF1324, AU1RF2804, AU1RF1404Z, AU1RF4104, AU1RF1010Z, and AU1RF3710Z

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Modules Optimize Cost-Performance Ratio For Appliance Motor Drives, STMicroelectronics' STGIPS10K60A, STGIPS14K60, STGIPL14K60, and STGIPS20K60 Intelligent power modules (IPMs)

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June 2010:

Power Block Boosts Efficiency, Saves Space Versus Discrete MOSFETs, Texas Instruments' CSD86350Q5D Power Block

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DrMOS Module Delivers Over 90% Efficiency, Alpha and Omega Semiconductor's AOZ5006 6-mm x 6-mm DrMOS power module

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July 2010:

150-V MOSFET Enhances Performance Of Isolated DC-DC Converters, Fairchild Semiconductor's FDMS86200 150-V trench power MOSFET

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November 2010:

1200-V SiC Schottky Family Features 30-A Device In TO-247, SemiSouth Laboratories' family of 1200-V SiC power Schottky diodes

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High-Temperature Controller And Driver Improve Performance Of SiC

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Switches, Cissoid's high-temperature Themis controller and Atlas push-pull driver stage

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MOSFET Package Delivers Top-Side Cooling In Industry-Standard Footprints, Fairchild Semiconductor's Dual Cool MOSFET packaging

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September 2009:

MOSFETs Minimize Gate Charge For Industrial Applications, IR's 150-V and 200-V HEXFET power MOSFETs, models include IRFB4615PBF and IRFB4620PBF

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1-A, 200-V Ultrafast Rectifier Comes in MicroSMP, Vishay's MUH1Px surface-mount 1-A ultrafast rectifiers

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MOSFET Reduces On-Resistance in Tiny CSP, Fairchild Semiconductor's FDZ371PZ p-channel PowerTrench MOSFET

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October 2009:

Intelligent Power Module Sets New Mark for Power Delivery, Powerex's DIP-IPM family including models PS21A7A ,PS21A79, and PS22A72 to PS22A78-E

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November 2009:

600-V Silicon Rectifiers Approach SiC Performance, QSpeed's H-series 600-V silicon rectifiers including models QH03TZ600, QH05TZ600, QH08TZ600, and QH12TZ600

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Dual SiC MOSFET Modules Promise High Efficiency, Powerex's QJD1210006 and QJD1210007 1200-V, 100-A MOSFET modules

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Automotive-Qualified IGBT Improves Thermal Performance, International Rectifier's AU1RG7CH80K6B-M is a 1200-V IGBT



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December 2009:

Power Devices Perform At Extreme Temperatures, Cissoid's CHT-NMOS40xx 40-V MOSFETs,

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